

**ARTICLE COMPRISING GATED FIELD EMISSION STRUCTURES WITH
CENTRALIZED NANOWIRES AND METHOD FOR MAKING THE SAME**

Inventor: Sungho Jin, 13634 Old El Camino Real, San Diego, CA 92130

CROSS REFERENCE TO RELATED APPLICATIONS

This application claims the benefit of the following United States provisional patent applications and is a continuation-in part of the following United States Utility Patent Applications:

1. U.S. Provisional Application Serial No. 60/405,561 filed by S. Jin on August 23, 2002 and entitled "MEMs Based Two-Dimensional E-Beam Nanolithography Device and Method For Making the Same";

2. U.S. Provisional Application Serial No. 60/441,437 filed by S. Jin on January 21, 2003 and entitled "Article Comprising A Gated Field Emission Structure With Centralized Nanowires and Method for Making the Same";

3. U.S. Utility Patent Application Serial No. 10/350,614 filed by S. Jin on January 24, 2003, ^{PAT 6,909,465} and entitled "Article Comprising MEMs-Based Two Dimensional E-Beam Sources and Method for Making the Same";

4. U.S. Utility Patent Application Serial No. 10/350,642 filed by S. Jin on January 24, 2003 and entitled "MEMs-Based Two Dimensional E-Beam Nano Lithography Device and Method for Making the Same";

5. U.S. Utility Patent Application Serial No. 10/357,004 filed by S. Jin on February 3, 2003 and entitled "Method for Fabricating Spaced-Apart Nanostructures";
and